Jiadi Zhu

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Soft-lock drawing of super-aligned carbon nanotube bundles for nanometre electrical contacts. Nature Nanotechnology, 2022, 17, 278-284. | 31.5 | 24 |
| 2 | Designing artificial two-dimensional landscapes via atomic-layer substitution. Proceedings of the National Academy of Sciences of the United States of America, 2021, 118, . | 7.1 | 43 |
| 3 | Highly Uniform Twoâ€Terminal Artificial Synapses Based on Polycrystalline Hf 0.5 Zr 0.5 O 2 for Sparsified Back Propagation Networks. Advanced Electronic Materials, 2020, 6, 2000204. | 5.1 | 4 |
| 4 | A comprehensive review on emerging artificial neuromorphic devices. Applied Physics Reviews, 2020, 7, | 11.3 | 417 |
| 5 | Brain-inspired computing with memristors: Challenges in devices, circuits, and systems. Applied Physics Reviews, 2020, 7, . | 11.3 | 217 |
| 6 | Stochastic neuron based on IGZO Schottky diodes for neuromorphic computing. APL Materials, 2019, 7, | 5.1 | 35 |
| 7 | Conductance quantization in oxide-based resistive switching devices. , 2019, , . | | 0 |
| 8 | Physically Transient True Random Number Generators Based on Paired Threshold Switches Enabling Monte Carlo Method Applications. IEEE Electron Device Letters, 2019, 40, 1096-1099. | 3.9 | 26 |
| 9 | Dual-Gated MoS ₂ Neuristor for Neuromorphic Computing. ACS Applied Materials & Interfaces, 2019, 11, 41482-41489. | 8.0 | 78 |
| 10 | Interfacial redox processes in memristive devices based on valence change and electrochemical metallization. Faraday Discussions, 2019, 213, 41-52. | 3.2 | 18 |
| 11 | Ion Gated Synaptic Transistors Based on 2D van der Waals Crystals with Tunable Diffusive Dynamics. Advanced Materials, 2018, 30, e1800195. | 21.0 | 368 |
| 12 | New Insights Into Energy Efficiency of Tunnel FET With Awareness of Source Doping Gradient Variation. IEEE Transactions on Electron Devices, 2018, 65, 2003-2009. | 3.0 | 6 |
| 13 | Vertical WS2/SnS2 van der Waals Heterostructure for Tunneling Transistors. Scientific Reports, 2018, 8, 17755. | 3.3 | 40 |
| 14 | Bipolar to unipolar mode transition and imitation of metaplasticity in oxide based memristors with enhanced ionic conductivity. Journal of Applied Physics, 2018, 124, . | 2.5 | 19 |
| 15 | Voltage-Controlled Magnetoresistance in Silicon Nanowire Transistors. Scientific Reports, 2018, 8, 15194. | 3.3 | 6 |
| 16 | Combinational Access Tunnel FET SRAM for Ultra-Low Power Applications. , 2018, , . | | 10 |
| 17 | Neuromorphic Computing: Ion Gated Synaptic Transistors Based on 2D van der Waals Crystals with Tunable Diffusive Dynamics (Adv. Mater. 21/2018). Advanced Materials, 2018, 30, 1870149. | 21.0 | 20 |
| 18 | Resistive switching and synaptic plasticity in HfO <inf>2</inf> -based memristors with single-layer and bilayer structures. , 2018, , . | | 2 |

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|----|--|-----|-----------|
| 19 | Benchmarking of multi-finger Schottky-Barrier tunnel FET for ultra-low power applications. , 2018, , . | | 0 |
| 20 | A Novel Tunnel FET Design Through Adaptive Bandgap Engineering With Constant Sub-Threshold Slope Over 5 Decades of Current and High \$ext{I}_{mathrm {ON}}/ext{I}_{mathrm {OFF}} Ratio. IEEE Electron Device Letters, 2017, 38, 540-543. | 3.9 | 39 |
| 21 | Design and Simulation of a Novel Graded-Channel Heterojunction Tunnel FET With High \${I} _{scriptscriptstyleext {ON}}/{I} _{scriptscriptstyleext {OFF}}\$ Ratio and Steep Swing. IEEE Electron Device Letters, 2017, 38, 1200-1203. | 3.9 | 28 |
| 22 | New Understanding of Random Telegraph Noise Amplitude in Tunnel FETs. IEEE Transactions on Electron Devices, 2017, 64, 3324-3330. | 3.0 | 11 |
| 23 | Deep insights into dielectric breakdown in tunnel FETs with awareness of reliability and performance co-optimization. , 2016, , . | | 2 |